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Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PowerPAK® SO-8L

PRODUCT SUMMARY				
V _{DS} (V)	100			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0197			
I _D (A) ^e	38			
Configuration	Single			
Package	PowerPAK SO-8L			

Bottom View

Top View

FEATURES

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Q_{gd}/Q_{gs} ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



	O _D
	+
G _O	_ → †
N-Channel MOSFET	o _s

ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJ118EP (for detailed order number please see www.vishay.com/doc?79776)

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V _{DS}	100	V	
Gate-source voltage		V_{GS}	± 20		
Continuous drain current ^e	T _C = 25 °C	- I _D	38		
	T _C = 125 °C		22		
Continuous source current (diode conduction) e		I _S	50	Α	
Pulsed drain current b, e		I _{DM}	84	l	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	22		
Single pulse avalanche energy	L = 0.1 IIII	E _{AS}	24	mJ	
Maximum power dissipation b, e	T _C = 25 °C	P _D	500	W	
	T _C = 125 °C	PD	166		
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C	
Soldering recommendations (peak temperature) c			260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount a	R_{thJA}	42	°C/W
Junction-to-case (drain) ^d	on-to-case (drain) ^d		2	C/VV

Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (www.vishay.com/doc?73257). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. As per JESD51-14
- e. Values based on RthJC and TC of 25 °C. Actual values achievable will be dependent on the thermal characteristics of the complete system



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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static							•	
Drain-source breakdown voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \mu A$		100	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2.7	3.5	V	
Gate-source leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 80 V	-	-	10		
Zero gate voltage drain current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 80 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$	-	-	50	μΑ	
		$V_{GS} = 0 V$	V _{DS} = 80 V, T _J = 175 °C	-	-	250		
On-state drain current a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α	
		V _{GS} = 10 V	I _D = 15 A	-	0.0164	0.0197	Ω	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = 10 V	I _D = 15 A, T _J = 125 °C	-	-	0.0405		
		V _{GS} = 10 V	I _D = 15 A, T _J = 175 °C	-	-	0.0510		
Forward transconductance b	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 20 \text{ A}$		-	60	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{GS} = 0 V V _{DS} = 25 V, f = 1 MHz	-	2073	2903	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	230	322		
Reverse transfer capacitance	C_{rss}			-	8	12		
Total gate charge ^c	Q_g			-	31	47	nC	
Gate-source charge c	Q_{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 50 \text{ V}, I_{D} = 6 \text{ A}$	-	9	-		
Gate-drain charge c	Q_{gd}			-	7	-		
Gate resistance	R_g	f = 1 MHz		0.6	1.2	1.8	Ω	
Turn-on delay time ^c	t _{d(on)}				12	18	ns	
Rise time ^c	t _r	V_{DD} = 50 V, R _L = 8.33 Ω I _D \cong 6 A, V _{GEN} = 10 V, R _g = 1 Ω		-	3	6		
Turn-off delay time ^c	t _{d(off)}			-	22	33		
Fall time ^c	t _f				4	8		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed current ^a	I _{SM}				-	84	Α	
Forward voltage	V _{SD}	I _F =	I _F = 15 A, V _{GS} = 0 V		-	1.1	V	
Body diode reverse recovery time	t _{rr}	I _F = 5 A, di/dt = 100 A/μs		-	38	76	ns	
Body diode reverse recovery charge	Q _{rr}			-	54	108	nC	
Reverse recovery fall time	t _a			-	29	-	ns	
Reverse recovery rise time	t _b			-	9	-		
Body diode peak reverse recovery current	I _{RM(REC)}			-	-2.4	-	Α	

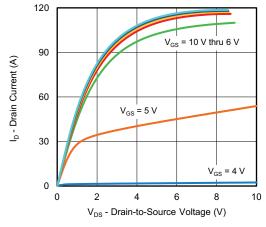
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

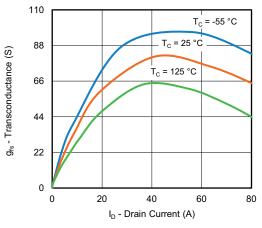
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



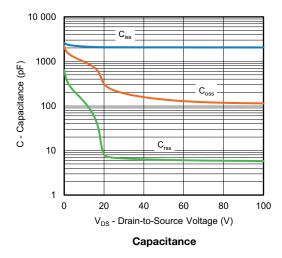
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

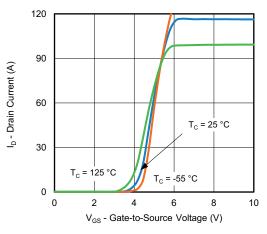




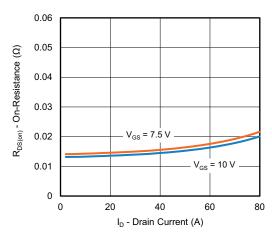


Transconductance

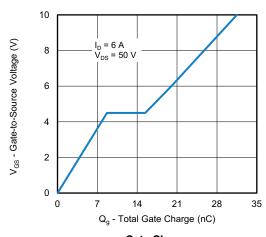




Transfer Characteristics

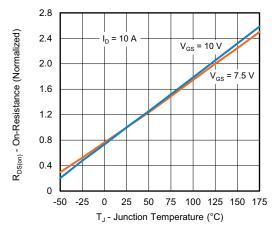


On-Resistance vs. Drain Current

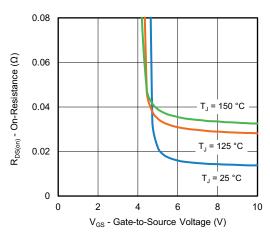




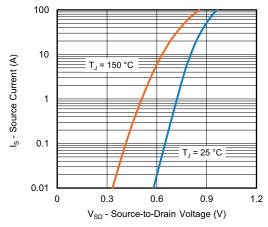
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature

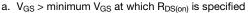


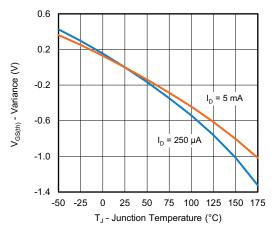
On-Resistance vs. Gate-to Source Voltage



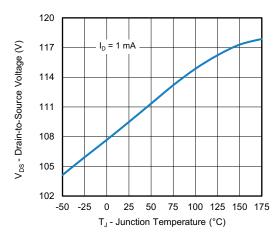
Source Drain Diode Forward Voltage

Note

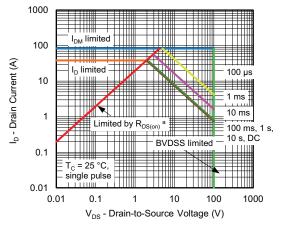




Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

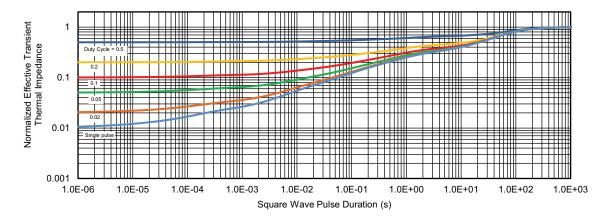


Safe Operating Area

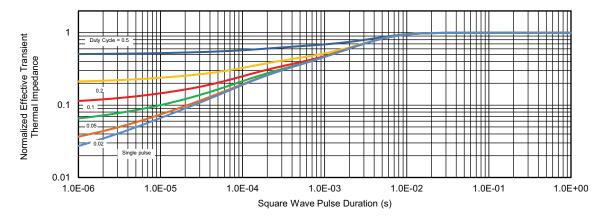
For technical questions, contact: automostech



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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